# UTC UNISONIC TECHNOLOGIES CO., LTD

**BTB16 Preliminary TRIAC** 

# **16A TRIACS**

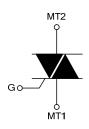
### DESCRIPTION

The UTC BTB16 is a 16A triacs which can be operated in 4 quadrants, it uses UTC's advanced technology to provide customers with high commutation performances and voltage insulated tab, etc.

The UTC BTB16 is suitable for AC switching application and phase control application such as fan speed and temperature modulation control, lighting control and static switching relay, either in through-hole or surface-mount packages.

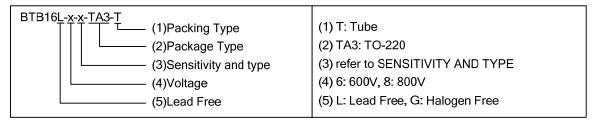
# TO-220

### **SYMBOL**



### **ORDERING INFORMATION**

| Ordering Number  |                  | Dookogo | Pin . | Assignn | Doolsing |         |  |
|------------------|------------------|---------|-------|---------|----------|---------|--|
| Lead Free        | Halogen Free     | Package | 1     | 2       | 3        | Packing |  |
| BTB16L-x-x-TA3-T | BTB16G-x-x-TA3-T | TO-220  | MT1   | MT2     | G        | Tube    |  |

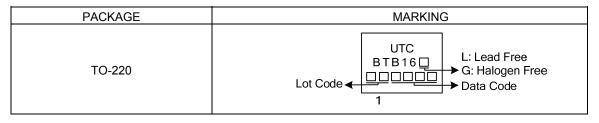


# **SENSITIVITY AND TYPE**

|                       | VOL | ΓAGE        | OENOITIV/ITV | TVDE     |  |  |
|-----------------------|-----|-------------|--------------|----------|--|--|
| PART NUMBER 600V 800V |     | SENSITIVITY | TYPE         |          |  |  |
| В                     | 0   | 0           | 50mA         | STANDARD |  |  |
| С                     | 0   |             | 25mA         | STANDARD |  |  |

### ⊚: Available

### MARKING INFORMATION



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### ■ ABSOLUTE MAXIMUM RATINGS

| PARAMETER  |                      |                       | SYMBOL            | RATINGS                                 | UNIT   |
|--|----------------------|-----------------------|-------------------|---|--------|
| RMS On-State Current (Full Sine Wave) T <sub>C</sub> =86°C                             |                      | $I_{T(RMS)}$          | 16                | Α                                       |        |
| Non Repetitive Surge Peak On-State Current (Full                                       | F=50 Hz              | t=20ms                | I <sub>TSM</sub>  | 160                                     | Α      |
| Cycle, T <sub>J</sub> initial=25°C)  | F=60 Hz              | t=16.7ms              | TISM              | 168                                     | Α      |
| I <sup>2</sup> t Value for Fusing  | t <sub>P</sub> =10ms |                       | l <sup>2</sup> t  | 144                                     | $A^2s$ |
| Critical Rate of Rise of On-State Current I <sub>G</sub> =2xI <sub>GT</sub> , tr≤100ns | F=120 Hz             | T <sub>J</sub> =125°C | dI/dt             | 50                                      | A/µs   |
| Non Repetitive Surge Peak<br>Off-State Voltage   | t <sub>P</sub> =10ms | T <sub>J</sub> =25°C  | $V_{DSM}/V_{RSM}$ | V <sub>DRM</sub> /V <sub>RRM</sub> +100 | V      |
| Peak Gate Current  | t <sub>P</sub> =20µs | T <sub>J</sub> =125°C | $I_{GM}$          | 4                                       | Α      |
| Average Gate Power Dissipation T <sub>J</sub> =125°C                                   |                      | $P_{G(AV)}$           | 1                 | W                                       |        |
| Operating Junction Temperature   |                      | $T_J$                 | -40~+125          | °C                                      |        |
| Storage Junction Temperature   |                      | $T_{STG}$             | -40~+150          | °C                                      |        |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### **■ THERMAL RESISTANCES**

| PARAMETER             | SYMBOL        | RATINGS | UNIT |  |
|-----------------------|---------------|---------|------|--|
| Junction to Ambient   | $\theta_{JA}$ | 60      | °C/W |  |
| Junction to Case (AC) | $\theta_{JC}$ | 1.2     | °C/W |  |

# ■ **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> =25°C unless otherwise specified.)

FOR STANDARD TYPE (4 QUADRANTS)

|   | SYMBOL         | TEST CONDITIONS   |          | С   |     |     | В   |     |     | LINIT |
|---|----------------|---|----------|-----|-----|-----|-----|-----|-----|-------|
| PARAMETER SYMBO   |                | TEST CONDITIONS   |          | MIN | TYP | MAX | MIN | TYP | MAX | UNIT  |
| Gate Trigger Current  |                |   | 1-11-111 |     |     | 25  |     |     | 50  | mA    |
| (Note 1)  | $I_{GT}$       | $V_D=12V$ , $R_L=33\Omega$  | IV       |     |     | 50  |     |     | 100 | mA    |
| Gate Trigger Voltage  | $V_{GT}$       |   | ALL      |     |     | 1.3 |     |     | 1.3 | V     |
| Gate Non-Trigger<br>Voltage                                       | $V_{GD}$       | $V_D=V_{DRM}$ , $R_L=3.3k\Omega$ , $T_J=125^{\circ}C$                     | ALL      | 0.2 |     |     | 0.2 |     |     | V     |
| Holding Current (Note 2)  | l <sub>Η</sub> | I <sub>T</sub> =500mA   |          |     |     | 25  |     |     | 50  | mA    |
| Latabia a Commant   | 1 -1 01        | I-III-IV  |          |     | 40  |     |     | 60  | mA  |       |
| Latching Current  | IL             | I <sub>G</sub> =1.2I <sub>GT</sub>  |          |     |     | 80  |     |     | 120 | mA    |
| Critical Rate of Rise of Off-State Voltage (Note 2)               | dV/dt          | V <sub>D</sub> =67%V <sub>DRM</sub> , Gate Open,<br>T <sub>J</sub> =125°C |          | 200 |     |     | 400 |     |     | V/µs  |
| Critical Rate of Rise of Off-State Voltage at Commutation(Note 2) | (dV/dt)c       | (dl/dt)c=7A/ms, T <sub>J</sub> = 12                                       | 5°C      | 5   |     |     | 10  |     |     | V/µs  |

## ■ STATIC CHARACTERISTICS

| PARAMETER                         | SYMBOL           | TEST CONDITIONS                                 |                       | MIN | TYP | MAX  | UNIT |
|-----------------------------------|------------------|---|-----------------------|-----|-----|------|------|
| Peak On-State Voltage(Note 2)     | $V_{TM}$         | $I_{TM}$ =22.5A, $t_p$ =380 $\mu$ s $T_J$ =25°C |                       |     |     | 1.55 | V    |
| Threshold Voltage(Note 2)         | $V_{TO}$         |   | T <sub>J</sub> =125°C |     |     | 0.85 | V    |
| Dynamic Resistance(Note 2)        | $R_D$            |   | T <sub>J</sub> =125°C |     |     | 25   | mΩ   |
| Repetitive Peak Off-State Current | I <sub>DRM</sub> | V V   | TJ=25°C               |     |     | 5    | μΑ   |
|                                   | I <sub>RRM</sub> | $V_{DRM}=V_{RRM}$                               | T <sub>J</sub> =125°C |     |     | 2    | mA   |

Note: 1. Minimum  $I_{\text{GT}}$  is guaranteed at 5% of  $I_{\text{GT}}$  max.

2. For both polarities of MT2 referenced to MT1.

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